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## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email \& Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, \#122 Zhenhua RD., Futian, Shenzhen, China

TOPFET high side switch

## DESCRIPTION

Monolithic temperature and overload protected power switch based on MOSFET technology in a 5 pin plastic surface mount envelope, configured as a single high side switch.

## APPLICATIONS

General controller for driving lamps, motors, solenoids, heaters.

## FEATURES

- Vertical power DMOS switch
- Low on-state resistance
- 5 V logic compatible input
- Overtemperature protection self resets with hysteresis
- Overload protection against short circuit load with output current limiting; latched - reset by input
- High supply voltage load protection
- Supply undervoltage lock out
- Status indication for overload protection activated
- Diagnostic status indication of open circuit load
- Very low quiescent current
- Voltage clamping for turn off of inductive loads
- ESD protection on all pins
- Reverse battery and overvoltage protection

PINNING - SOT426

| PIN | DESCRIPTION |
| :---: | :--- |
| 1 | Ground |
| 2 | Input |
| 3 | (connected to mb) |
| 4 | Status |
| 5 | Load |
| mb | Battery |

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MIN. | UNIT |
| :---: | :---: | :---: | :---: |
| $\mathrm{I}_{\mathrm{L}}$ | Nominal load current (ISO) | 6 | A |
| SYMBOL | PARAMETER | MAX. | UNIT |
| $V_{B G}$ | Continuous off-state supply voltage | 50 | V |
|  | Continuous load current | 15 | A |
| $\mathrm{T}_{\mathrm{j}}$ | Continuous junction temperature | 150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{R}_{\text {ON }}$ | On-state resistance | 60 | $\mathrm{m} \Omega$ |

## FUNCTIONAL BLOCK DIAGRAM



Fig.1. Elements of the TOPFET HSS with internal ground resistor.

## PIN CONFIGURATION



SYMBOL


## TOPFET high side switch

## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $V_{B G}$ | Battery voltages <br> Continuous off-state supply voltage | - | 0 | 50 | V |
| $\begin{array}{\|l\|l\|} \hline-V_{\mathrm{BG}} \\ -\mathrm{V}_{\mathrm{BG}} \\ \hline \end{array}$ | Reverse battery voltages ${ }^{1}$ <br> Repetitive peak supply voltage Continuous reverse supply voltage | External resistors: $\begin{aligned} & R_{l}=R_{S} \geq 4.7 \mathrm{k} \Omega, \delta \leq 0.1 \\ & R_{I}=R_{S} \geq 4.7 \mathrm{k} \Omega \end{aligned}$ |  | $\begin{aligned} & 32 \\ & 16 \end{aligned}$ | $\begin{aligned} & \text { V } \\ & \text { V } \end{aligned}$ |
| $\begin{array}{\|l\|} \hline \mathrm{L}_{\mathrm{L}} \\ \mathrm{P}_{\mathrm{D}} \\ \mathrm{~T}_{\text {stg }} \\ \mathrm{T}_{\mathrm{j}} \\ \mathrm{~T}_{\text {sold }} \end{array}$ | Continuous load current <br> Total power dissipation <br> Storage temperature <br> Continuous junction temperature ${ }^{2}$ <br> Lead temperature | $\begin{aligned} & \mathrm{T}_{\mathrm{mb}} \leq 115^{\circ} \mathrm{C} \\ & \mathrm{~T}_{\mathrm{mb}} \leq 25^{\circ} \mathrm{C} \\ & - \\ & - \\ & \text { during soldering } \end{aligned}$ | $-55$ | $\begin{gathered} 15 \\ 83.3 \\ 175 \\ 150 \\ 250 \end{gathered}$ | $\begin{aligned} & \hline \mathrm{A} \\ & \mathrm{~W} \\ & { }^{\circ} \mathrm{C} \\ & { }^{\circ} \mathrm{C} \\ & { }^{\circ} \mathrm{C} \end{aligned}$ |
| $\begin{array}{\|l} I_{1} \\ I_{\mathrm{S}} \\ I_{\mathrm{I}} \\ I_{\mathrm{S}} \end{array}$ | Input and status <br> Continuous input current Continuous status current <br> Repetitive peak input current Repetitive peak status current | $\begin{aligned} & \delta \leq 0.1 \\ & \delta \leq 0.1 \end{aligned}$ | $\begin{gathered} -5 \\ -5 \\ -20 \\ -20 \end{gathered}$ | $\begin{gathered} 5 \\ 5 \\ 20 \\ 20 \end{gathered}$ | $\begin{aligned} & \mathrm{mA} \\ & \mathrm{~mA} \\ & \mathrm{~mA} \\ & \mathrm{~mA} \end{aligned}$ |
| $\mathrm{E}_{\text {BL }}$ | Inductive load clamping <br> Non-repetitive clamping energy | $\mathrm{T}_{\mathrm{mb}}=150{ }^{\circ} \mathrm{C}$ prior to turn-off | - | 1.2 | J |

## ESD LIMITING VALUE

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
| :--- | :--- | :--- | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{C}}$ | Electrostatic discharge capacitor <br> voltage | Human body model; <br> $\mathrm{C}=250 \mathrm{pF} ; \mathrm{R}=1.5 \mathrm{k} \Omega$ | - | 2 | kV |

## THERMAL CHARACTERISTIC

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| :--- | :--- | :--- | :---: | :---: | :---: | :---: |
|  | Thermal resistance <br> $\mathrm{R}_{\mathrm{th} \mathrm{j}-\mathrm{mb}}$ | Junction to mounting base |  |  |  |  |

[^0]
## TOPFET high side switch

## STATIC CHARACTERISTICS

$\mathrm{T}_{\mathrm{mb}}=25^{\circ} \mathrm{C}$ unless otherwise stated

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\begin{aligned} & \mathrm{V}_{\mathrm{BG}} \\ & \mathrm{~V}_{\mathrm{BL}} \\ & -\mathrm{V}_{\mathrm{LG}} \end{aligned}$ | Clamping voltages <br> Battery to ground <br> Battery to load <br> Negative load to ground | $\begin{aligned} & \mathrm{I}_{\mathrm{G}}=1 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{L}}=\mathrm{I}_{\mathrm{G}}=1 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{L}}=1 \mathrm{~mA} \end{aligned}$ | $\begin{aligned} & 50 \\ & 50 \\ & 12 \end{aligned}$ | $\begin{aligned} & 55 \\ & 55 \\ & 17 \end{aligned}$ | $\begin{aligned} & 65 \\ & 65 \\ & 21 \end{aligned}$ | $\begin{aligned} & \mathrm{V} \\ & \mathrm{~V} \\ & \mathrm{~V} \end{aligned}$ |
| $V_{B G}$ | Supply voltage Operating range ${ }^{1}$ | battery to ground | 5 | - | 40 | V |
| $\begin{aligned} & \mathrm{I}_{\mathrm{L}} \\ & \mathrm{I}_{\mathrm{B}} \\ & \mathrm{I}_{\mathrm{G}} \\ & \mathrm{I}_{\mathrm{L}} \end{aligned}$ | Currents <br> Nominal load current ${ }^{2}$ Quiescent current ${ }^{3}$ Operating current ${ }^{4}$ Off-state load current ${ }^{5}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{BG}}=13 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{BL}}=0.5 \mathrm{~V} ; \mathrm{T}_{\mathrm{mb}}=85^{\circ} \mathrm{C} \\ & \mathrm{~V}_{\mathrm{IG}}=0 \mathrm{~V} ; \mathrm{V}_{\mathrm{LG}}=0 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{IG}}=5 \mathrm{~V} ; \mathrm{L}_{\mathrm{L}}=0 \mathrm{~A} \\ & \mathrm{~V}_{\mathrm{BL}}=13 \mathrm{~V} ; \mathrm{V}_{\mathrm{IG}}=0 \mathrm{~V} \end{aligned}$ | $\begin{gathered} 6 \\ - \\ 1.5 \end{gathered}$ | $\begin{aligned} & 0.1 \\ & 2.2 \\ & 0.1 \end{aligned}$ | $\begin{aligned} & 2 \\ & 4 \\ & 1 \end{aligned}$ | A <br> $\mu \mathrm{A}$ <br> mA <br> $\mu \mathrm{A}$ |
| $\begin{aligned} & \mathrm{R}_{\mathrm{ON}} \\ & \mathrm{R}_{\mathrm{ON}} \\ & \mathrm{R}_{\mathrm{G}} \\ & \hline \end{aligned}$ | Resistances <br> On-state resistance ${ }^{6}$ On-state resistance Internal ground resistance | $\begin{aligned} & \mathrm{V}_{\mathrm{BG}}=13 \mathrm{~V} ; \mathrm{I}_{\mathrm{L}}=7.5 \mathrm{~A} ; \mathrm{t}_{\mathrm{p}}=300 \mu \mathrm{~s} \\ & \mathrm{~V}_{\mathrm{BG}}=5 \mathrm{~V} ; \mathrm{I}_{\mathrm{L}}=1.5 \mathrm{~A} ; \mathrm{t}_{\mathrm{p}}=300 \mu \mathrm{~s} \\ & \mathrm{I}_{\mathrm{G}}=10 \mathrm{~mA} \end{aligned}$ | - | $\begin{gathered} 45 \\ 70 \\ 150 \\ \hline \end{gathered}$ | $\begin{aligned} & 60 \\ & 90 \end{aligned}$ | $\begin{gathered} \mathrm{m} \Omega \\ \mathrm{~m} \Omega \\ \Omega \end{gathered}$ |

## INPUT CHARACTERISTICS

$\mathrm{T}_{\mathrm{mb}}=25^{\circ} \mathrm{C} ; \mathrm{V}_{\mathrm{BG}}=13 \mathrm{~V}$

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| :--- | :--- | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{I}_{\mathrm{I}}$ | Input current | $\mathrm{V}_{\mathrm{IG}}=5 \mathrm{~V}$ | 35 | 60 | 100 | $\mu \mathrm{~A}$ |
| $\mathrm{~V}_{\text {IG }}$ | Input clamping voltage | $\mathrm{I}_{\mathrm{I}}=200 \mu \mathrm{AA}$ | 6 | 7.5 | 8.5 | V |
| $\mathrm{~V}_{\text {IG(ON) }}$ | Input turn-on threshold voltage |  | - | 2.1 | 2.7 | V |
| $\mathrm{~V}_{\text {IG(OFF) }}$ | Input turn-off threshold voltage |  | 1.5 | 2 | - | V |

[^1]
## PROTECTION FUNCTIONS AND STATUS INDICATIONS

Truth table for normal, open-circuit load and overload conditions and abnormal supply voltages.

| FUNCTIONS |  | TRUTH TABLE |  |  | THRESHOLD |  |  | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SYMBOL | CONDITION | INPUT | STATUS | OUTPUT | MIN. | TYP. | MAX. |  |
|  | Normal on-state | 1 | 1 | 1 |  |  |  |  |
|  | Normal off-state | 0 | 1 | 0 |  |  |  |  |
| $\mathrm{I}_{\text {LOC })}$ | Open circuit load ${ }^{1}$ | 1 | 0 | 1 | 100 | 350 | 600 | mA |
|  | Open circuit load | 0 | 1 | 0 |  |  |  |  |
| $\mathrm{T}_{\mathrm{j} \text { (T) }}$ | Over temperature ${ }^{2}$ | 1 | 0 | 0 | 150 | 175 | - | ${ }^{\circ} \mathrm{C}$ |
|  | Over temperature ${ }^{3}$ | 0 | 0 | 0 |  |  |  |  |
| $\mathrm{V}_{\text {ВL(т) }}$ | Short circuit load ${ }^{4}$ | 1 | 0 | 0 | 9 | 10.5 | 12 | V |
|  | Short circuit load | 0 | 1 | 0 |  |  |  |  |
| $V_{\text {BG(T) }}$ | Low supply voltage ${ }^{5}$ | X | 1 | 0 | 3 | 4 | 5 | V |
| $\mathrm{V}_{\mathrm{BGG}(\mathrm{P})}$ | High supply voltage ${ }^{6}$ | X | 1 | 0 | 40 | 45 | 50 | V |

For input ' 0 ' equals low, ' 1 ' equals high, ' $X$ ' equals don't care.
For status ' 0 ' equals low, ' 1 ' equals open or high.
For output switch ' 0 ' equals off, '1' equals on.

## STATUS CHARACTERISTICS

$\mathrm{T}_{\mathrm{mb}}=25^{\circ} \mathrm{C}$.
The status output is an open drain transistor, and requires an external pull-up circuit to indicate a logic high.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| :--- | :--- | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{SG}}$ | Status clamping voltage | $\mathrm{I}_{\mathrm{S}}=100 \mu \mathrm{~A} ; \mathrm{V}_{\mathrm{IG}}=0 \mathrm{~V}$ | 6 | 7 | 8 | V |
| $\mathrm{~V}_{\mathrm{SG}}$ | Status low voltage | $\mathrm{I}_{\mathrm{S}}=50 \mu \mathrm{~A} ; \mathrm{V}_{\mathrm{BG}}=13 \mathrm{~V} ; \mathrm{V}_{\mathrm{IG}}=5 \mathrm{~V}$ | - | 0.7 | 0.8 | V |
| $\mathrm{I}_{\mathrm{S}}$ | Status leakage current | $\mathrm{V}_{\mathrm{SG}}=5 \mathrm{~V}$ | - | 0.1 | 1 | $\mu \mathrm{~A}$ |
| $\mathrm{I}_{\mathrm{S}}$ | Status saturation current $^{7}$ | $\mathrm{~V}_{\mathrm{SS}}=5 \mathrm{~V} ; \mathrm{R}_{\mathrm{S}}=0 \Omega ; \mathrm{V}_{\mathrm{BG}}=13 \mathrm{~V}$ | - | 5 | - | mA |
|  | Application information |  |  |  |  |  |
| $\mathrm{R}_{\mathrm{S}}$ | External pull-up resistor $^{8}$ | $\mathrm{~V}_{\mathrm{SS}}=5 \mathrm{~V}$ | - | 100 | - | $\mathrm{k} \Omega$ |

[^2]
## TOPFET high side switch

## SMD version of BUK201-50Y

## DYNAMIC CHARACTERISTICS

$\mathrm{T}_{\mathrm{mb}}=25^{\circ} \mathrm{C} ; \mathrm{V}_{\mathrm{BG}}=13 \mathrm{~V}$

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $-\mathrm{V}_{\text {LG }}$ | Inductive load turn-off Negative load voltage ${ }^{1}$ | $\mathrm{V}_{\mathrm{IG}}=0 \mathrm{~V} ; \mathrm{I}_{\mathrm{L}}=7.5 \mathrm{~A} ; \mathrm{t}_{\mathrm{P}}=300 \mu \mathrm{~s}$ | 15 | 20 | 25 | V |
| $\begin{aligned} & \mathrm{t}_{\mathrm{dsc}} \\ & \mathrm{I}_{\mathrm{L}} \end{aligned}$ | Short circuit load protection ${ }^{2}$ <br> Response time <br> Load current prior to turn-off | $\begin{aligned} & \mathrm{V}_{\mathrm{IG}}=5 \mathrm{~V} ; \mathrm{R}_{\mathrm{L}} \leq 10 \mathrm{~m} \Omega \\ & \mathrm{t}<\mathrm{t}_{\mathrm{dsc}} \end{aligned}$ | - | $\begin{aligned} & 90 \\ & 42 \end{aligned}$ | - | $\begin{gathered} \mu \mathrm{s} \\ \mathrm{~A} \end{gathered}$ |
| $\mathrm{IL}_{\text {Llim) }}$ | Overload protection ${ }^{3}$ <br> Load current limiting | $\mathrm{V}_{\mathrm{BL}}=9 \mathrm{~V} ; \mathrm{t}_{\mathrm{p}}=300 \mu \mathrm{~s}$ | 28 | 40 | 52 | A |

## SWITCHING CHARACTERISTICS

$\mathrm{T}_{\mathrm{mb}}=25^{\circ} \mathrm{C}, \mathrm{V}_{B G}=13 \mathrm{~V}$, for resistive load $\mathrm{R}_{\mathrm{L}}=13 \Omega$.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\mathrm{d} \text { on }}$ <br> $\mathrm{dV} / \mathrm{dt}_{\mathrm{on}}$ <br> ton | During turn-on <br> Delay time Rate of rise of load voltage <br> Total switching time | $\begin{aligned} & \text { to } \mathrm{V}_{\mathrm{IG}}=5 \mathrm{~V} \\ & \text { to } 10 \% \mathrm{~V}_{\mathrm{L}} \\ & \text { to } 90 \% \mathrm{~V}_{\mathrm{L}} \end{aligned}$ | - | $\begin{gathered} 16 \\ 1 \\ 40 \end{gathered}$ | $2.5$ | $\mu \mathrm{s}$ <br> $\mathrm{V} / \mu \mathrm{s}$ <br> $\mu \mathrm{s}$ |
| $t_{\text {d off }}$ <br> $\mathrm{dV} / \mathrm{dt}_{\text {off }}$ <br> $\mathrm{t}_{\text {off }}$ | During turn-off <br> Delay time <br> Rate of fall of load voltage <br> Total switching time | $\begin{aligned} & \text { to } \mathrm{V}_{\mathrm{IG}}=0 \mathrm{~V} \\ & \text { to } 90 \% \mathrm{~V}_{\mathrm{L}} \\ & \text { to } 10 \% \mathrm{~V}_{\mathrm{L}} \end{aligned}$ | - | $\begin{gathered} 30 \\ 1.2 \\ 50 \end{gathered}$ | $2.5$ | $\begin{gathered} \mu \mathrm{s} \\ \mathrm{~V} / \mu \mathrm{s} \\ \mu \mathrm{~s} \end{gathered}$ |

## CAPACITANCES

$\mathrm{T}_{\mathrm{mb}}=25^{\circ} \mathrm{C} ; \mathrm{f}=1 \mathrm{MHz} ; \mathrm{V}_{\mathrm{IG}}=0 \mathrm{~V}$

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| :--- | :--- | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{C}_{\mathrm{i}}$ | Input capacitance | $\mathrm{V}_{\mathrm{BG}}=13 \mathrm{~V}$ | - | 15 | 20 | pF |
| $\mathrm{C}_{\mathrm{bl}}$ | Output capacitance | $\mathrm{V}_{\mathrm{BL}}=\mathrm{V}_{\mathrm{BG}}=13 \mathrm{~V}$ | - | 415 | 580 | pF |
| $\mathrm{C}_{\mathrm{sg}}$ | Status capacitance | $\mathrm{V}_{\mathrm{SG}}=5 \mathrm{~V}$ | - | 11 | 15 | pF |

[^3]
## TOPFET high side switch



Fig.4. High side switch measurements schematic. (current and voltage conventions)


Fig.5. Normalised limiting power dissipation. $P_{D} \%=100 \cdot P_{D} / P_{D}\left(25{ }^{\circ} \mathrm{C}\right)=f\left(T_{m b}\right)$


Fig.6. Limiting continuous on-state load current. $I_{L}=f\left(T_{\text {mb }}\right)$; conditions: $V_{I G}=5 \mathrm{~V}, V_{B G}=13 \mathrm{~V}$


Fig.7. Typical on-state characteristics, $T_{j}=25^{\circ} \mathrm{C}$. $I_{L}=f\left(V_{B L}\right) ;$ parameter $V_{B G} ; t_{p}=250 \mu \mathrm{~s}$


Fig.8. Typical on-state resistance, $T_{i}=25^{\circ} \mathrm{C}$.
$R_{O N}=f\left(V_{B G}\right)$; conditions: $I_{L}=7.5 \mathrm{~A} ; t_{p}=300 \mu \mathrm{~s}$


Fig.9. Typical on-state resistance, $t_{p}=300 \mu \mathrm{~s}$. $R_{O N}=f\left(T_{j}\right) ;$ parameter $V_{B G} ;$ condition $I_{L}=1.5 \mathrm{~A}$

## TOPFET high side switch



Fig.10. Typical supply characteristics, $25^{\circ} \mathrm{C}$. $I_{G}=f\left(V_{B G}\right)$; parameter $V_{I G}$


Fig.11. Typical operating supply current.
$I_{G}=f\left(T_{j}\right)$; parameter $V_{B G}$; condition $V_{I G}=5 \mathrm{~V}$


Fig.12. Typical supply quiescent current. $I_{B}=f\left(T_{j}\right)$; condition $V_{B G}=13 \mathrm{~V}, V_{I G}=0 \mathrm{~V}, V_{L G}=0 \mathrm{~V}$


Fig.13. Typical off-state leakage current. $I_{L}=f\left(T_{j}\right)$; conditions: $V_{B L}=13 \mathrm{~V}=V_{B G} ; V_{I G}=0 \mathrm{~V}$.


Fig.14. Typical input characteristics, $T_{j}=25^{\circ} \mathrm{C}$. $I_{I}=f\left(V_{I G}\right)$; parameter $V_{B G}$


Fig.15. Typical input current, $T_{i}=25^{\circ} \mathrm{C}$. $I_{I}=f\left(V_{B G}\right)$; condition $V_{I G}=5 \mathrm{~V}$

TOPFET high side switch


Fig.19. Typical status leakage current. $I_{S}=f\left(T_{j}\right)$; conditions $V_{S G}=5 \mathrm{~V}, V_{I G}=V_{B G}=0 \mathrm{~V}$


Fig.20. Typical status low characteristic, $T_{T}=25^{\circ} \mathrm{C}$. $I_{S}=f\left(V_{S G}\right)$; conditions $V_{I G}=5 \mathrm{~V}, V_{B G}=13 \mathrm{~V}, I_{L}=0 \mathrm{~A}$


Fig.21. Typical status low voltage, $V_{S G}=f\left(T_{j}\right)$. conditions $I_{S}=50 \mu \mathrm{~A}, V_{I G}=5 \mathrm{~V}, V_{B G}=13 \mathrm{~V}, I_{L}=0 \mathrm{~A}$

## TOPFET high side switch



Fig.22. Typical status clamping voltage, $V_{S G}=f\left(T_{j}\right)$. parameter $V_{I G} ;$ conditions $I_{S}=100 \mu A, V_{B G}=13 \mathrm{~V}$


Fig.23. Low load current detection threshold.
$I_{L(O C)}=f\left(T_{j}\right)$; conditions $V_{I G}=5 \mathrm{~V} ; V_{B G}=13 \mathrm{~V}$


Fig.24. Supply typical undervoltage thresholds.
$V_{B G(T O)}=f\left(T_{j}\right)$; conditions $V_{I G}=3 \mathrm{~V} ; I_{L}=80 \mathrm{~mA}$


Fig.25. Supply typical overvoltage thresholds. $V_{B G(L P)}=f\left(T_{j}\right) ;$ conditions $V_{I G}=5 \mathrm{~V} ; I_{L}=80 \mathrm{~mA}$


Fig.26. Typical battery to ground clamping voltage. $V_{B G}=f\left(T_{j}\right) ;$ parameter $I_{G}$


Fig.27. Typical negative load clamping characteristic. $I_{L}=f\left(V_{L G}\right)$; conditions $V_{I G}=0 \mathrm{~V}, t_{p}=300 \mu \mathrm{~s}, 25^{\circ} \mathrm{C}$

## TOPFET high side switch



Fig.28. Typical negative load clamping voltage. $V_{L G}=f\left(T_{j}\right) ;$ parameter $I_{L} ;$ condition $V_{I G}=0 \mathrm{~V}$.


Fig.29. Typical battery to load clamping voltage.
$V_{B L}=f\left(T_{j}\right) ;$ parameter $I_{L} ;$ condition $I_{G}=5 \mathrm{~mA}$.


Fig.30. Typical reverse battery characteristic. $I_{G}=f\left(V_{B G}\right)$; conditions $I_{L}=0 A, T_{j}=25^{\circ} \mathrm{C}$


Fig.31. Typical reverse diode characteristic. $I_{L}=f\left(V_{B L}\right)$; conditions $V_{I G}=0 \mathrm{~V}, T_{j}=25^{\circ} \mathrm{C}$


Fig.32. Typical output capacitance. $T_{m b}=25^{\circ} \mathrm{C}$ $C_{b l}=f\left(V_{B L}\right)$; conditions $f=1 \mathrm{MHz}, V_{I G}=0 \mathrm{~V}$


Fig.33. Typical overload characteristic, $T_{m b}=25^{\circ} \mathrm{C}$. $I_{L}=f\left(V_{B L}\right)$; condition $V_{B G}=13 \mathrm{~V}$; parameter $t_{p}$

## TOPFET high side switch



Fig.34. Typical overload current, $V_{B L}=9 \mathrm{~V}$. $I_{L}=f\left(T_{m b}\right)$; conditions $V_{B G}=13 \mathrm{~V} ; t_{p}=300 \mu \mathrm{~s}$


Fig.35. Typical short circuit load threshold voltage. $V_{B L(T))}=f\left(V_{B G}\right)$; condition $T_{m b}=25^{\circ} \mathrm{C}$


Fig.36. Typical short circuit load threshold voltage. $V_{B L(T O)}=f\left(T_{\text {mb }}\right)$; condition $V_{B G}=13 \mathrm{~V}$


Fig.37. Transient thermal impedance.
$Z_{t h j-m b}=f(t) ;$ parameter $D=t_{p} / T$

## MECHANICAL DATA

Dimensions in mm
Net Mass: 1.5 g


Fig.38. SOT426
mounting base connected to centre pin (cropped short)

MOUNTING INSTRUCTIONS


Fig.39. SOT426
soldering pattern for surface mounting.

TOPFET high side switch

## DEFINITIONS

| Data sheet status |  |
| :--- | :--- |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one <br> or more of the limiting values may cause permanent damage to the device. These are stress ratings only and <br> operation of the device at these or at any other conditions above those given in the Characteristics sections of <br> this specification is not implied. Exposure to limiting values for extended periods may affect device reliability. |
| Application information |  |
| Where application information is given, it is advisory and does not form part of the specification. |  |
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## LIFE SUPPORT APPLICATIONS

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[^0]:    1 Reverse battery voltage is allowed only with external input and status resistors to limit the currents to a safe value.
    2 For normal continuous operation. A higher $T_{j}$ is allowed as an overload condition but at the threshold $T_{j(T))}$ the over temperature trip operates to protect the switch.
    3 Of the output Power MOS transistor.

[^1]:    1 On-state resistance is increased if the supply voltage is less than 9 V . Refer to figure 8.
    2 Defined as in ISO 10483-1.
    3 This is the continuous current drawn from the battery when the input is low and includes leakage current to the load.
    4 This is the continuous current drawn from the battery with no load connected, but with the input high.
    5 The measured current is in the load pin only.
    6 The supply and input voltage for the $\mathrm{R}_{\mathrm{ON}}$ tests are continuous. The specified pulse duration $\mathrm{t}_{\mathrm{p}}$ refers only to the applied load current.

[^2]:    1 In the on-state, the switch detects whether the load current is less than the quoted open load threshold current. This is for status indication only. Typical hysteresis equals 140 mA . The thresholds are specified for supply voltage within the normal working range.
    2 After cooling below the reset temperature the switch will resume normal operation. The reset temperature is lower than the trip temperature by typically $10{ }^{\circ} \mathrm{C}$.
    3 If the overtemperature protection has operated, status remains low to indicate the overtemperature condition even if the input is taken low, providing the device has not cooled below the reset temperature.
    4 After short circuit protection has operated, the input voltage must be toggled low for the switch to resume normal operation.
    5 Undervoltage sensor causes the device to switch off. Typical hysteresis equals 0.7 V .
    6 Overvoltage sensor causes the device to switch off to protect the load. Typical hysteresis equals 1.3 V .
    7 In a fault condition with the pull-up resistor short circuited while the status transistor is conducting.
    8 The pull-up resistor also protects the status pin during reverse battery conditions.

[^3]:    1 For a high side switch, the load pin voltage goes negative with respect to ground during the turn-off of an inductive load. This negative voltage is clamped by the device.
    2 The load current is self-limited during the response time for short circuit load protection. Response time is measured from when input goes high.
    3 If the load resistance is low, but not a complete short circuit, such that the on-state voltage remains less than $V_{B L(T O)}$, the device remains in current limiting until the overtemperature protection operates.

